



PATENT 81839.0105 #4

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Masanori KIMURA

Serial No: 10/030,867

Filed: October 18, 2001

For: METHOD FOR GROWING
SEMICONDUCTOR SINGLE
CRYSTAL

Art Unit: Not Assigned

Examiner: Not Assigned

4A
B4
6/7/02

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PRELIMINARY AMENDMENT

U.S. Patent and Trademark Office
P. O. Box 2327
Arlington, VA 22202

Dear Sir:

Prior to examination of above-identified application, please amend the
application as follows:

IN THE CLAIMS:

Rewrite claim 3 as follows:

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3. (Amended) The method for growing a semiconductor single crystal
according to Claim 1, wherein electric power values of the heater surrounding the
crucible and the subsidiary heating means and/or a ratio of the both power values are
obtained by calculation based on global heat transfer analysis, the obtained value(s)
is/are used as a target value or values of control, and electric powers supplied to the
heater and the subsidiary heating means are controlled to be as near the target value
or values as possible during the pulling of the single crystal.